

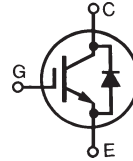
# High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

## IXBA10N300HV IXBH10N300HV

$$V_{CES} = 3000V$$

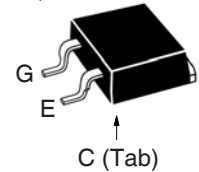
$$I_{C110} = 10A$$

$$V_{CE(sat)} \leq 2.8V$$

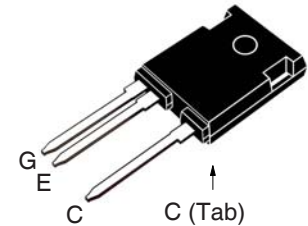


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_C = 25^\circ C$ to $150^\circ C$	3000	V
$V_{CGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GE} = 1M\Omega$	3000	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ C$	34	A
$I_{C110}$	$T_C = 110^\circ C$	10	A
$I_{CM}$	$T_C = 25^\circ C$ , 1ms	88	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15V$ , $T_{VJ} = 125^\circ C$ , $R_G = 10\Omega$ Clamped Inductive Load	$I_{CM} = 80$ 1500	A V
<b><math>T_{SC}</math></b> <b>(SCSOA)</b>	$V_{GE} = 15V$ , $T_J = 125^\circ C$ , $R_G = 82\Omega$ , $V_{CE} = 1500V$ , Non-Repetitive	10	$\mu s$
$P_C$	$T_C = 25^\circ C$	180	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$F_C$	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
$M_d$	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
<b>Weight</b>	TO-263HV	2.5	g
	TO-247HV	6.0	g

TO-263HV (IXBA)



TO-247HV (IXBH)



G = Gate      C = Collector  
E = Emitter    Tab = Collector

### Features

- High Blocking Voltage
- Anti-Parallel Diode
- Low Conduction Losses

### Advantages

- Low Gate Drive Requirement
- High Power Density

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{CES}$	$I_C = 250\mu A$ , $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$ , $V_{CE} = V_{GE}$	3.0		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 500 $\mu A$
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 10A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ C$		2.2 2.7	2.8 V

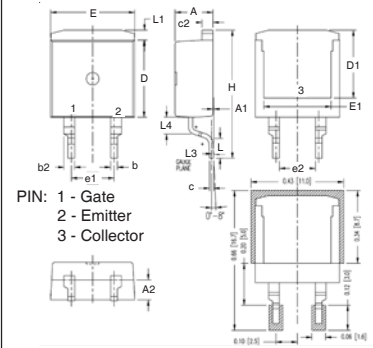
**Symbol Test Conditions**
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$ 
**Characteristic Values**

		Min.	Typ.	Max.		
$g_{fS}$	$I_C = 10A, V_{CE} = 10V, \text{Note 1}$	6	11		S	
$C_{ies}$	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$		1044		pF	
$C_{oes}$			42		pF	
$C_{res}$			14		pF	
$Q_g$	$I_C = 10A, V_{GE} = 15V, V_{CE} = 1000V$		46		nC	
$Q_{ge}$			5		nC	
$Q_{gc}$			20		nC	
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 10A, V_{GE} = 15V$		36		ns	
$t_r$			340		ns	
$t_{d(off)}$		$V_{CE} = 960V, R_G = 10\Omega$		100		ns
$t_f$				1850		ns
$t_{d(on)}$	<b>Resistive Switching Times, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 10A, V_{GE} = 15V$		40		ns	
$t_r$			765		ns	
$t_{d(off)}$		$V_{CE} = 960V, R_G = 10\Omega$		120		ns
$t_f$				2010		ns
$R_{thJC}$	TO-247HV			0.69	$^\circ\text{C/W}$	
$R_{thCS}$			0.21		$^\circ\text{C/W}$	

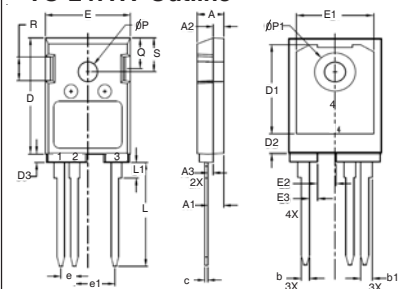
**Reverse Diode**
**Symbol Test Conditions**
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$ 
**Characteristic Values**

		Min.	Typ.	Max.	
$V_F$	$I_F = 10A, V_{GE} = 0V$			2.7	V
$t_{rr}$	$I_F = 5A, V_{GE} = 0V, -di_F/dt = 100A/\mu\text{s}$		1.6		$\mu\text{s}$
$I_{RM}$			23		A
$Q_{RM}$		$V_R = 100V, V_{GE} = 0V$		18.6	

 Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**TO-263HV-2L Outline**

 PIN: 1 - Gate  
 2 - Emitter  
 3 - Collector

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200	BSC	5.08	BSC
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010	BSC	0.254	BSC
(L4)	.071	.087	1.80	2.20

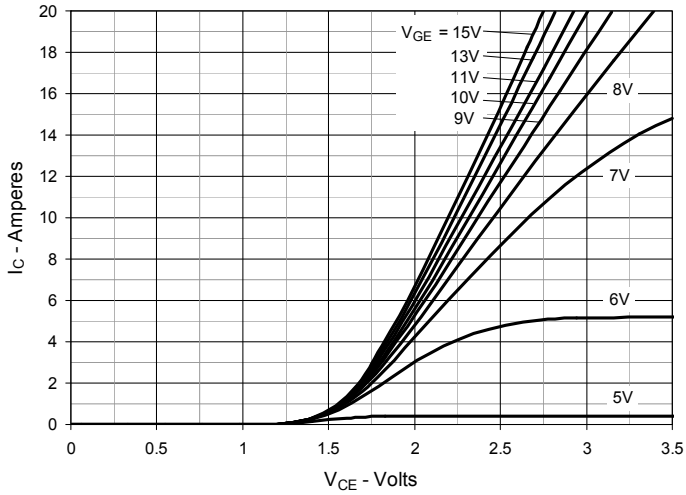
**TO-247HV Outline**

 PINS:  
 1 - Gate 2 - Emitter  
 3, 4 - Collector

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100	BSC	2.54	BSC
e1	.300	BSC	7.62	BSC
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
$\phi P$	.138	.142	3.50	3.60
$\phi P1$	.272	.280	6.90	7.10
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30
S	.240	.248	6.10	6.30

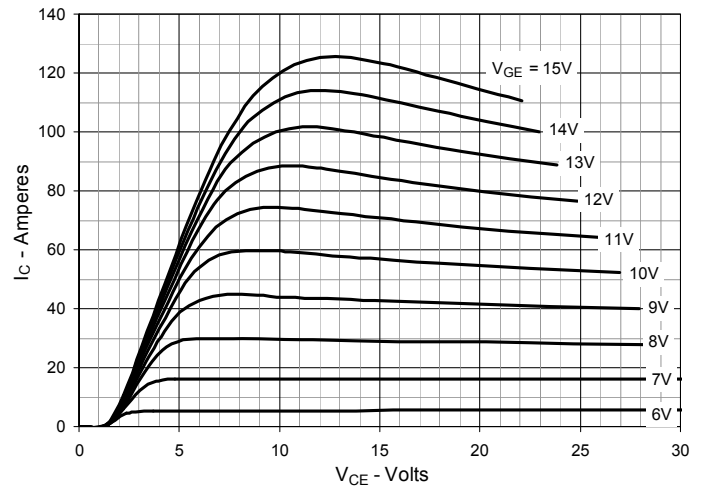
IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

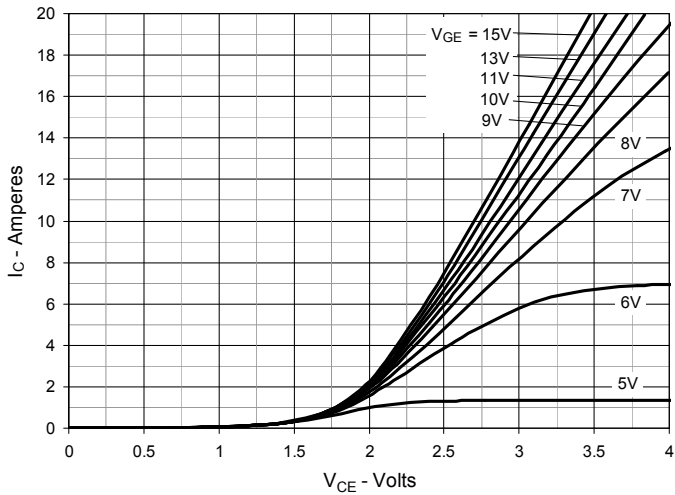
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



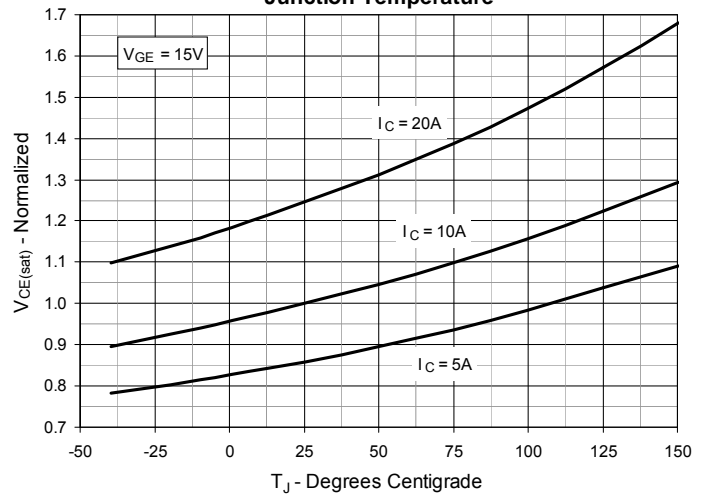
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



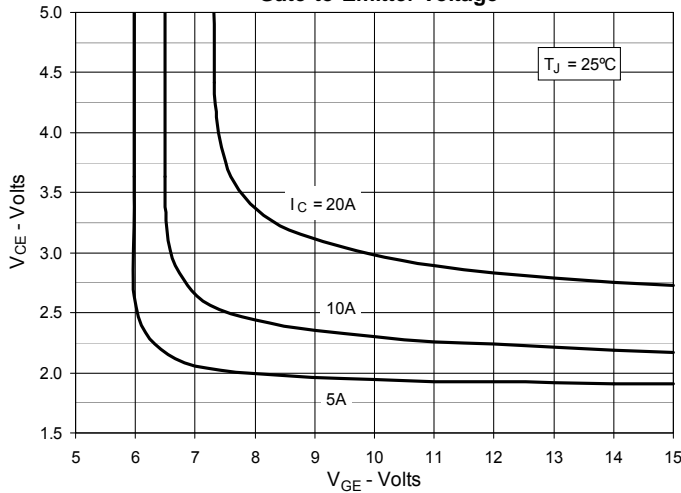
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



**Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature**



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage**



**Fig. 6. Input Admittance**

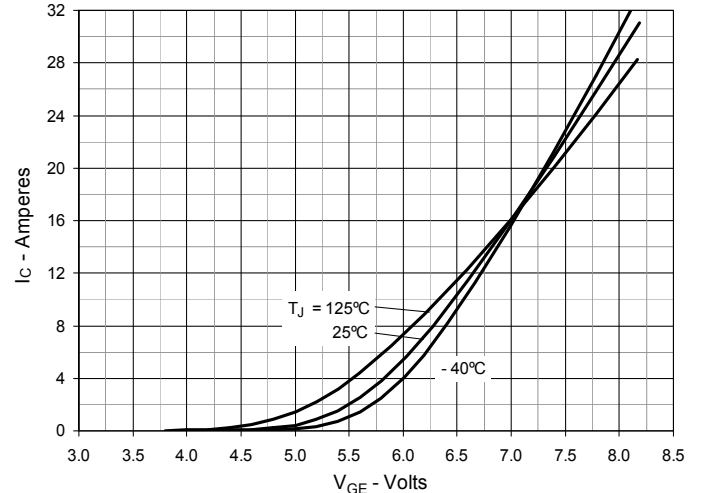


Fig. 7. Transconductance

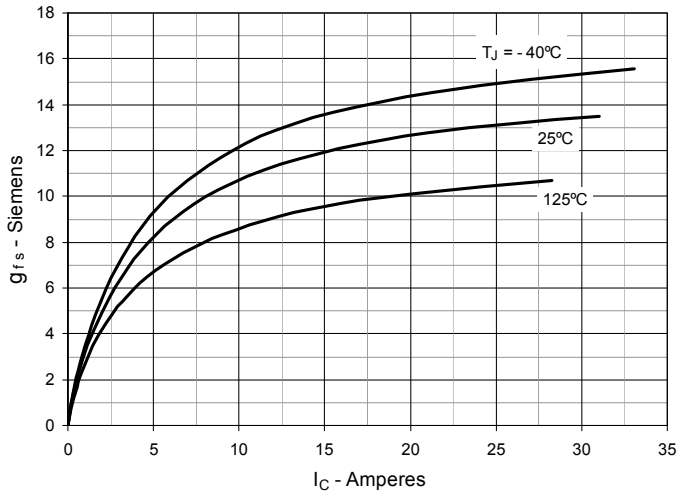


Fig. 8. Forward Voltage Drop of Intrinsic Diode

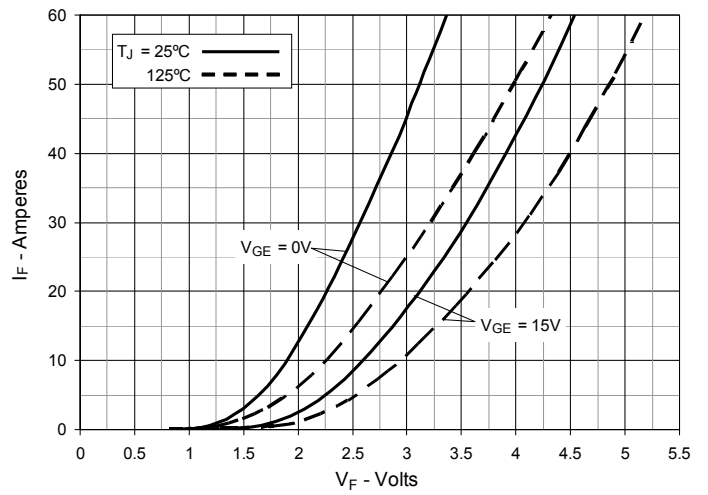


Fig. 9. Gate Charge

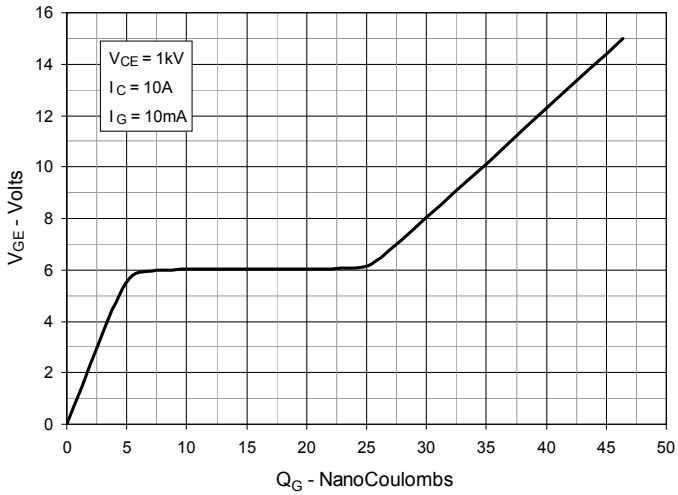


Fig. 10. Capacitance

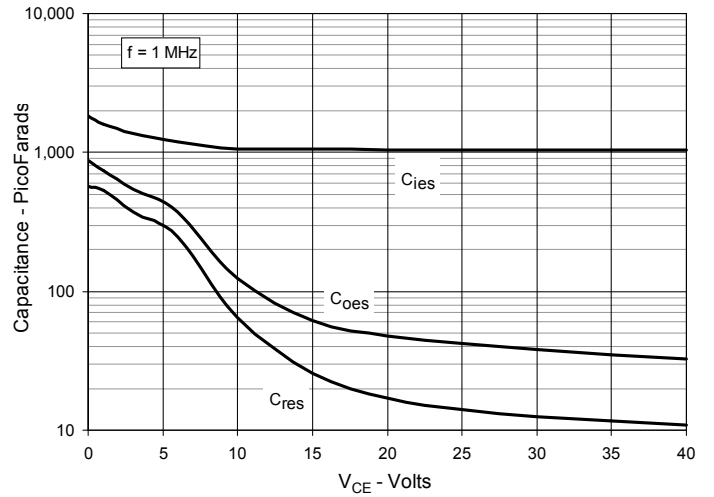


Fig. 11. Reverse-Bias Safe Operating Area

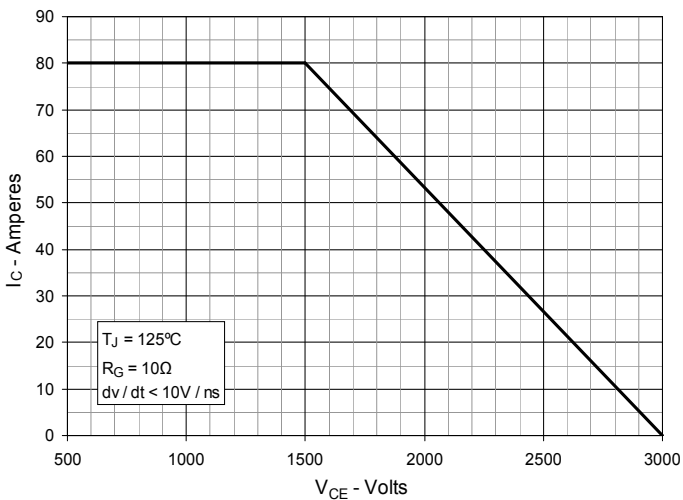
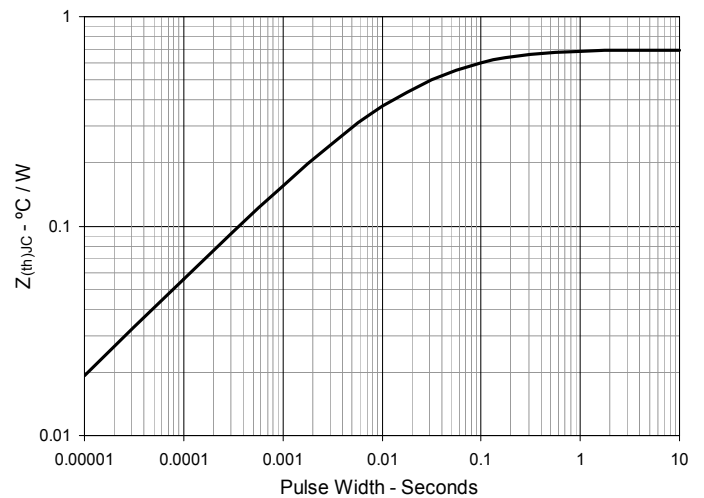
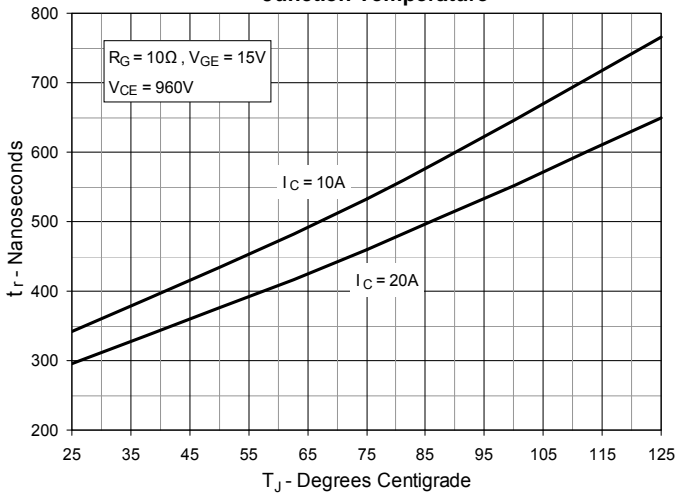


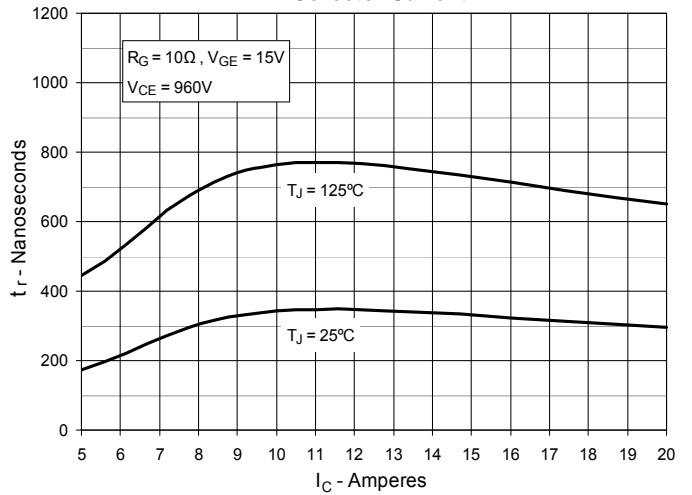
Fig. 12. Maximum Transient Thermal Impedance



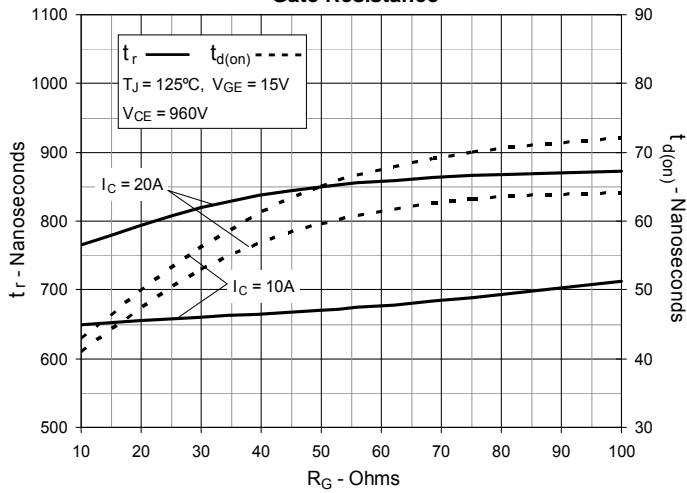
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



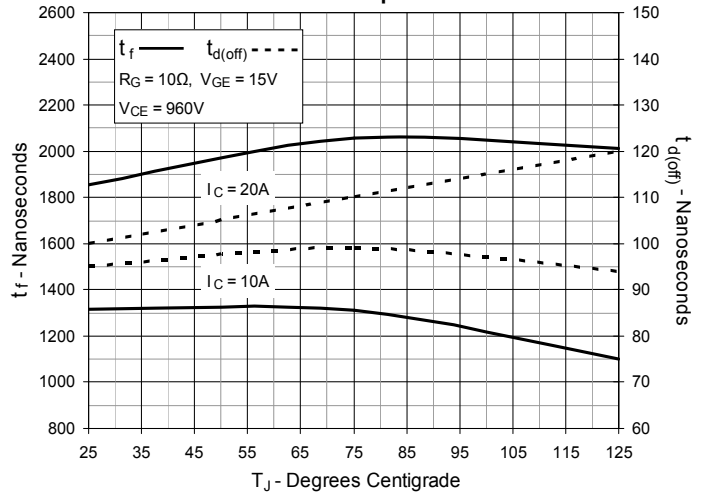
**Fig. 14. Resistive Turn-on Rise Time vs. Collector Current**



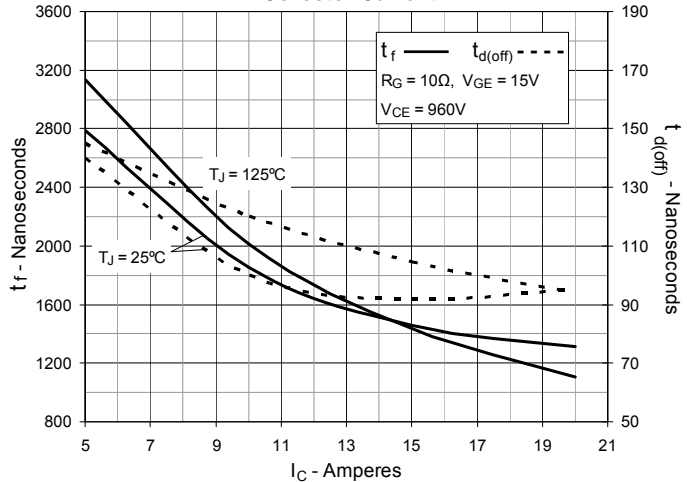
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



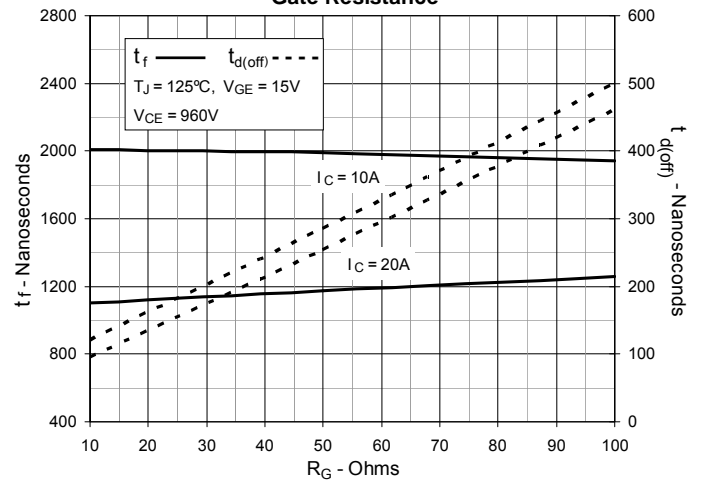
**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



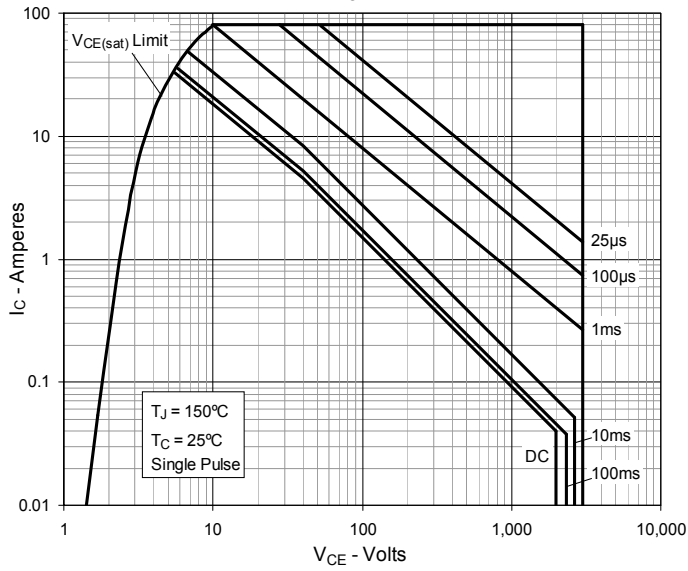
**Fig. 17. Resistive Turn-off Switching Times vs. Collector Current**



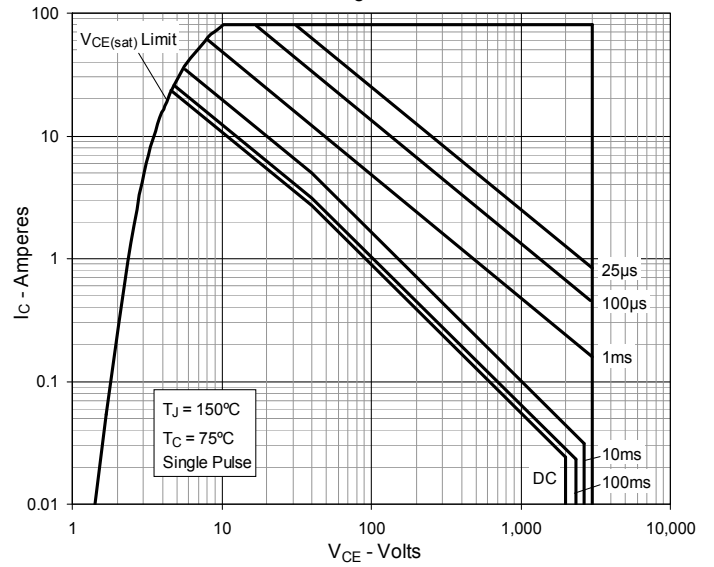
**Fig. 28. Resistive Turn-off Switching Times vs. Gate Resistance**



**Fig. 19. Forward-Bias Safe Operating Area**  
**@  $T_C = 25^\circ\text{C}$**



**Fig. 20. Forward-Bias Safe Operating Area**  
**@  $T_C = 75^\circ\text{C}$**



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